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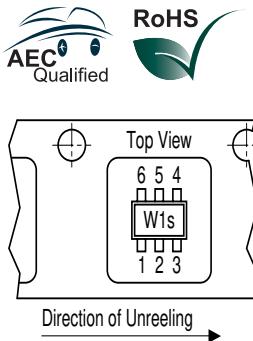
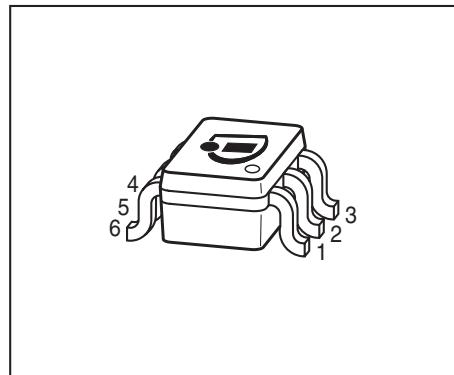
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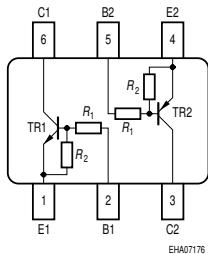
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## NPN/PNP Silicon Digital Transistor Array

- Switching circuit, inverter, interface circuit, driver circuit
- Two (galvanic) internal isolated NPN/PNP Transistors in one package
- Built in bias resistor  
NPN:  $R_1 = 47\text{k}\Omega$ ,  $R_2 = 47\text{k}\Omega$   
PNP:  $R_1 = 2.2\text{k}\Omega$ ,  $R_2 = 47\text{k}\Omega$
- Pb-free (RoHS compliant) package
- Qualified according AEC Q101



Marking on SOT-363 package  
(for example W1s)  
corresponds to pin 1 of device  
  
Position in tape: pin 1  
opposite of feed hole side



EHA07193

EHA07176

Type	Marking	Pin Configuration						Package
BCR48PN	WTs	1=E1	2=B1	3=C2	4=E2	5=B2	6=C1	SOT363

### Maximum Ratings

Parameter	Symbol	Value	Unit
Collector-emitter voltage	$V_{CEO}$	50	V
Collector-base voltage	$V_{CBO}$	50	
Input forward voltage NPN	$V_i(fwd)$	80	
Input forward voltage PNP	$V_i(fwd)$	20	
Input reverse voltage NPN	$V_i(rev)$	10	
Input reverse voltage PNP	$V_i(rev)$	5	
DC collector current NPN	$I_C$	70	mA
DC collector current PNP	$I_C$	100	
Total power dissipation, $T_S = 115^\circ\text{C}$	$P_{tot}$	250	mW
Junction temperature	$T_j$	150	$^\circ\text{C}$
Storage temperature	$T_{sta}$	-65...+150	

**Thermal Resistance**

Junction - soldering point <sup>1)</sup>	$R_{thJS}$	$\leq 140$	K/W
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**Electrical Characteristics at  $T_A=25^\circ\text{C}$ , unless otherwise specified**

Parameter	Symbol	Values			Unit
		min.	typ.	max.	

**DC Characteristics for NPN Type**

Collector-emitter breakdown voltage $I_C = 100 \mu\text{A}, I_B = 0$	$V_{(\text{BR})\text{CEO}}$	50	-	-	V
Collector-base breakdown voltage $I_C = 10 \mu\text{A}, I_E = 0$	$V_{(\text{BR})\text{CBO}}$	50	-	-	
Collector cutoff current $V_{CB} = 40 \text{ V}, I_E = 0$	$I_{\text{CBO}}$	-	-	100	nA
Emitter cutoff current $V_{EB} = 10 \text{ V}, I_C = 0$	$I_{\text{EBO}}$	-	-	164	$\mu\text{A}$
DC current gain 2) $I_C = 5 \text{ mA}, V_{CE} = 5 \text{ V}$	$h_{FE}$	70	-	-	-
Collector-emitter saturation voltage2) $I_C = 10 \text{ mA}, I_B = 0.5 \text{ mA}$	$V_{CE\text{sat}}$	-	-	0.3	V
Input off voltage $I_C = 100 \mu\text{A}, V_{CE} = 5 \text{ V}$	$V_{i(\text{off})}$	0.8	-	1.5	
Input on Voltage $I_C = 2 \text{ mA}, V_{CE} = 0.3 \text{ V}$	$V_{i(\text{on})}$	1	-	3	
Input resistor	$R_1$	32	47	62	$\text{k}\Omega$
Resistor ratio	$R_1/R_2$	0.9	1	1.1	-

**AC Characteristics for NPN Type**

Transition frequency $I_C = 10 \text{ mA}, V_{CE} = 5 \text{ V}, f = 100 \text{ MHz}$	$f_T$	-	100	-	MHz
Collector-base capacitance $V_{CB} = 10 \text{ V}, f = 1 \text{ MHz}$	$C_{cb}$	-	3	-	pF

<sup>1)</sup>For calculation of  $R_{thJA}$  please refer to Application Note AN077 (Thermal Resistance Calculation)

<sup>2)</sup>Pulse test:  $t < 300 \mu\text{s}$ ;  $D < 2\%$

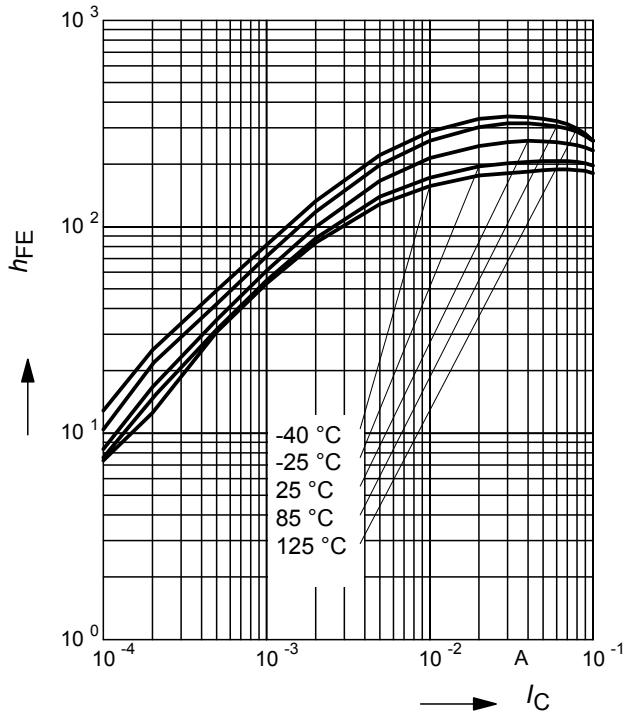
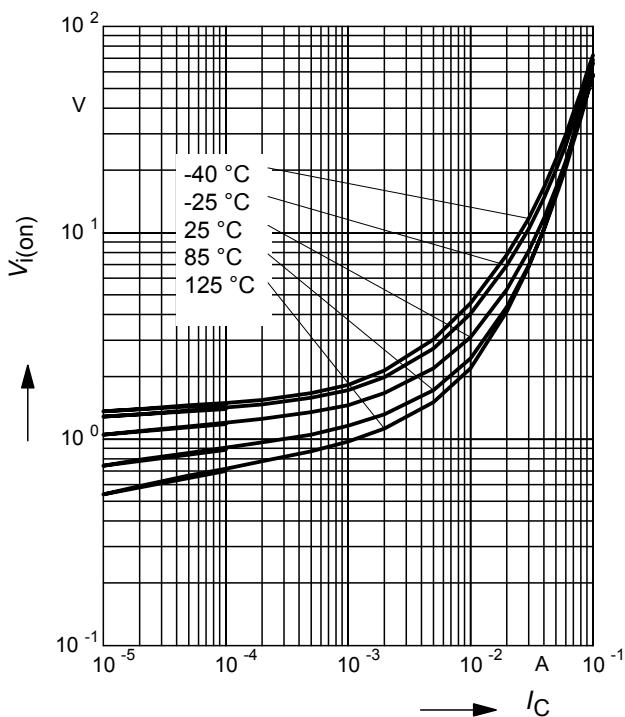
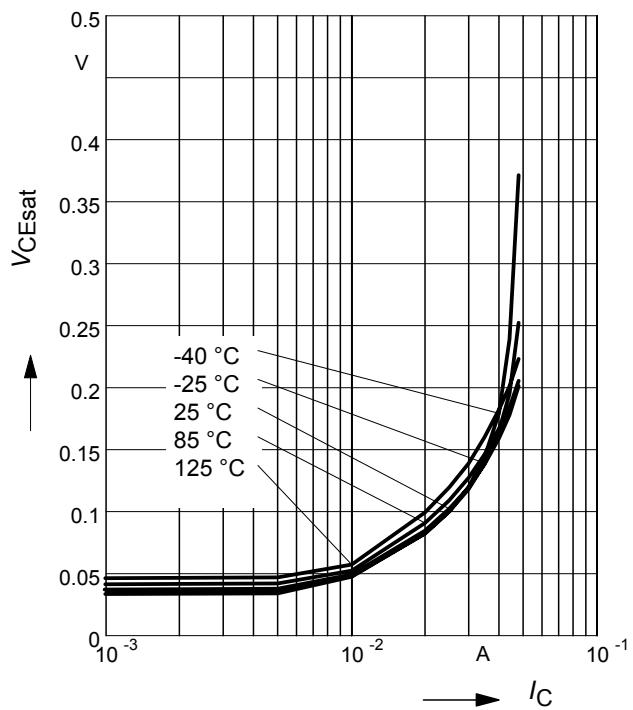
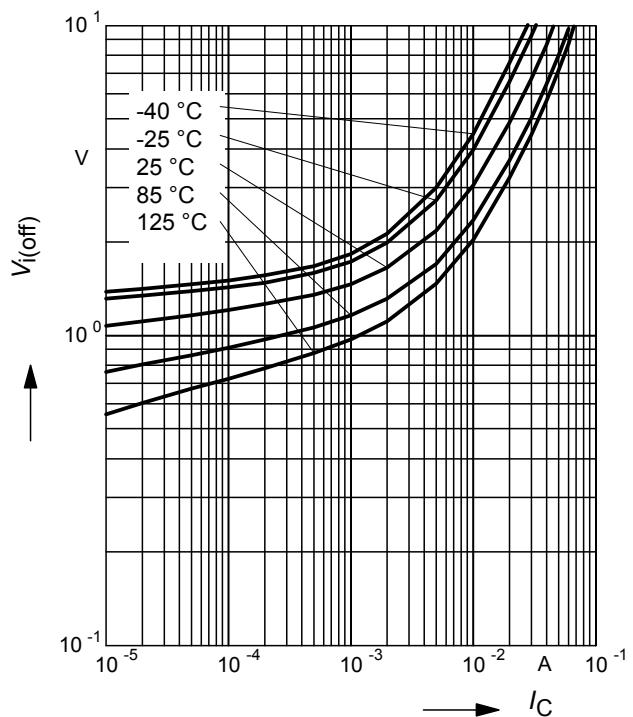
**Electrical Characteristics** at  $T_A=25^\circ\text{C}$ , unless otherwise specified

<b>Parameter</b>	<b>Symbol</b>	<b>Values</b>			<b>Unit</b>
		<b>min.</b>	<b>typ.</b>	<b>max.</b>	
<b>DC Characteristics for PNP Type</b>					
Collector-emitter breakdown voltage $I_C = 100 \mu\text{A}, I_B = 0$	$V_{(\text{BR})\text{CEO}}$	50	-	-	V
Collector-base breakdown voltage $I_C = 10 \mu\text{A}, I_E = 0$	$V_{(\text{BR})\text{CBO}}$	50	-	-	
Collector cutoff current $V_{CB} = 40 \text{ V}, I_E = 0$	$I_{\text{CBO}}$	-	-	100	nA
Emitter cutoff current $V_{EB} = 5 \text{ V}, I_C = 0$	$I_{\text{EBO}}$	-	-	164	μA
DC current gain 1) $I_C = 5 \text{ mA}, V_{CE} = 5 \text{ V}$	$h_{\text{FE}}$	70	-	-	-
Collector-emitter saturation voltage 1) $I_C = 10 \text{ mA}, I_B = 0.5 \text{ mA}$	$V_{\text{CEsat}}$	-	-	0.3	V
Input off voltage $I_C = 100 \mu\text{A}, V_{CE} = 5 \text{ V}$	$V_{i(\text{off})}$	0.4	-	0.8	
Input on voltage $I_C = 2 \text{ mA}, V_{CE} = 0.3 \text{ V}$	$V_{i(\text{on})}$	0.5	-	1.1	
Input resistor	$R_1$	1.5	2.2	2.9	kΩ
Resistor ratio	$R_1/R_2$	0.042	0.047	0.052	-

**AC Characteristics for PNP Type**

Transition frequency $I_C = 10 \text{ mA}, V_{CE} = 5 \text{ V}, f = 100 \text{ MHz}$	$f_T$	-	200	-	MHz
Collector-base capacitance $V_{CB} = 10 \text{ V}, f = 1 \text{ MHz}$	$C_{cb}$	-	3	-	pF

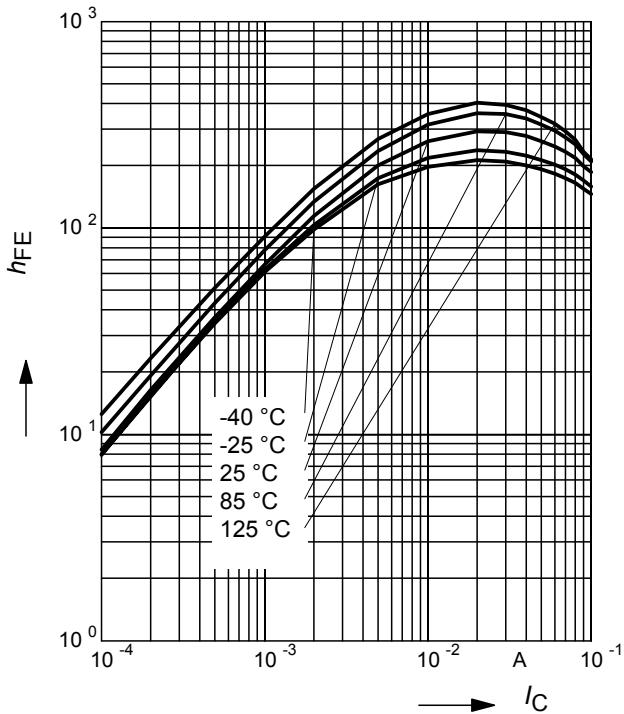
1) Pulse test:  $t < 300 \mu\text{s}$ ;  $D < 2\%$

**NPN Type**
**DC Current Gain**  $h_{FE} = f(I_C)$ 
 $V_{CE} = 5V$  (common emitter configuration)

**Input on Voltage**  $V_{i(on)} = f(I_C)$ 
 $V_{CE} = 0.3V$  (common emitter configuration)

**Collector-Emitter Saturation Voltage**
 $V_{CEsat} = f(I_C), h_{FE} = 20$ 

**Input off voltage**  $V_{i(off)} = f(I_C)$ 
 $V_{CE} = 5V$  (common emitter configuration)


## PNP Type

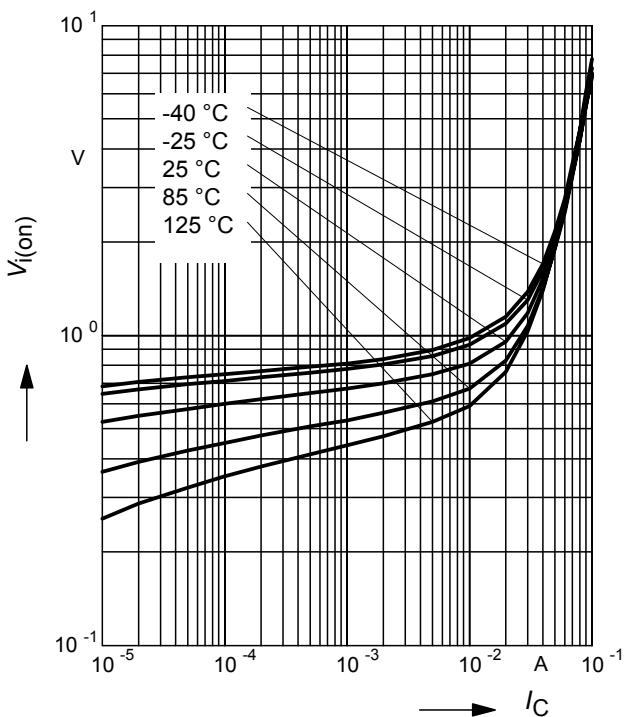
**DC Current Gain**  $h_{FE} = f(I_C)$

$V_{CE} = 5V$  (common emitter configuration)



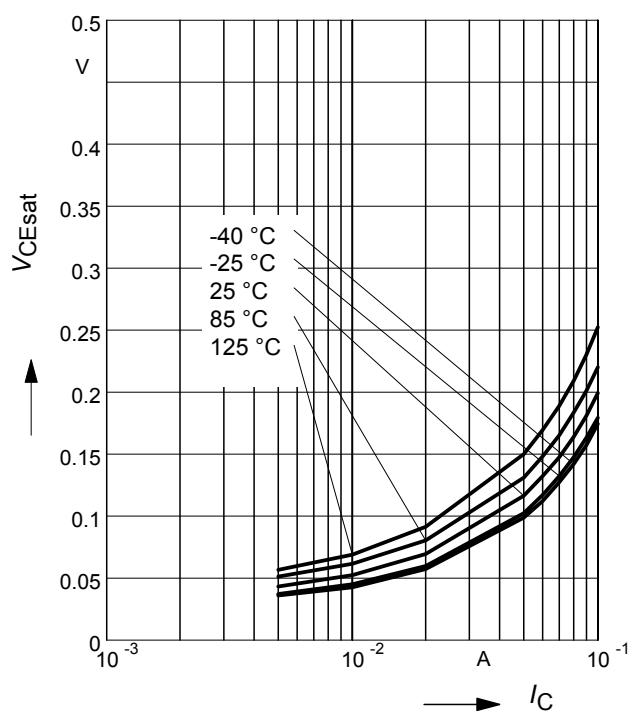
**Input on Voltage**  $V_{i(on)} = f(I_C)$

$V_{CE} = 0.3V$  (common emitter configuration)



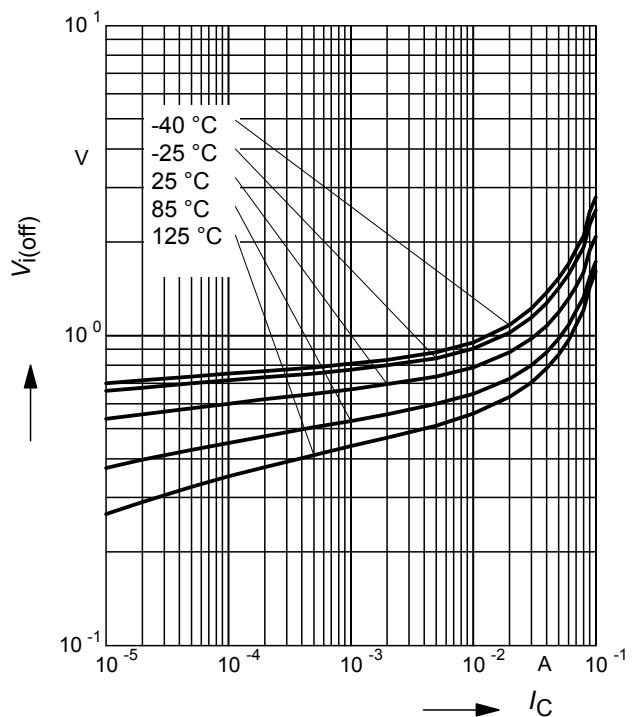
**Collector-Emitter Saturation Voltage**

$V_{CEsat} = f(I_C)$ ,  $h_{FE} = 20$

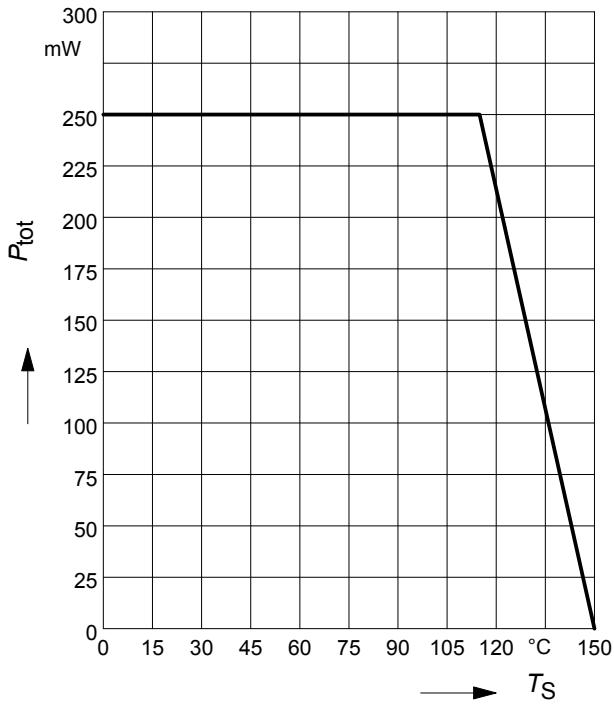


**Input off voltage**  $V_{i(off)} = f(I_C)$

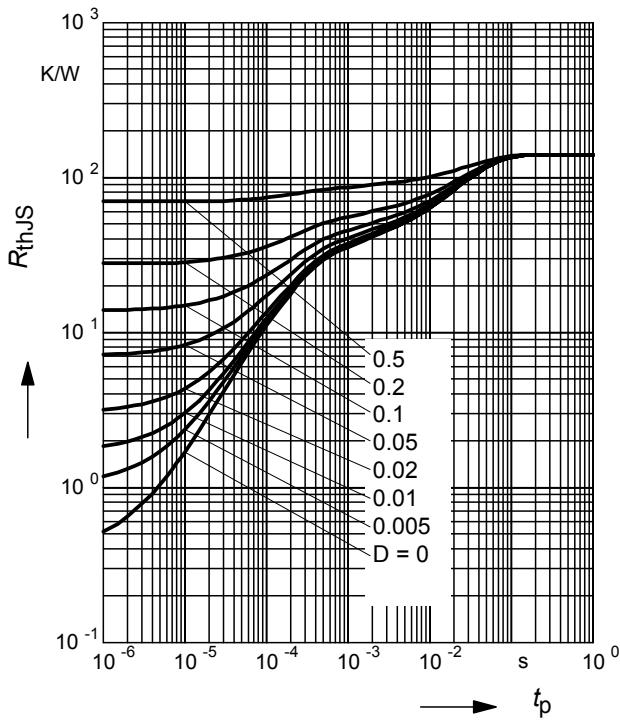
$V_{CE} = 5V$  (common emitter configuration)



**Total power dissipation  $P_{\text{tot}} = f(T_S)$**

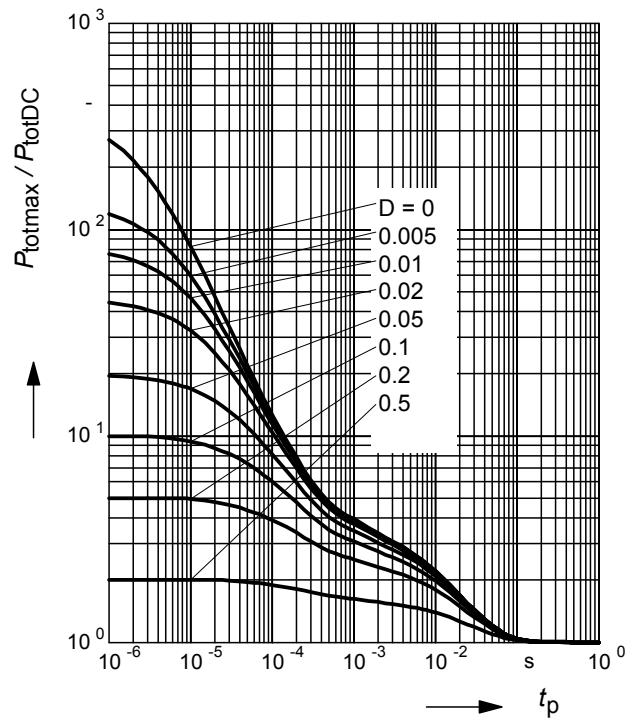


**Permissible Pulse Load  $R_{\text{thJS}} = f(t_p)$**

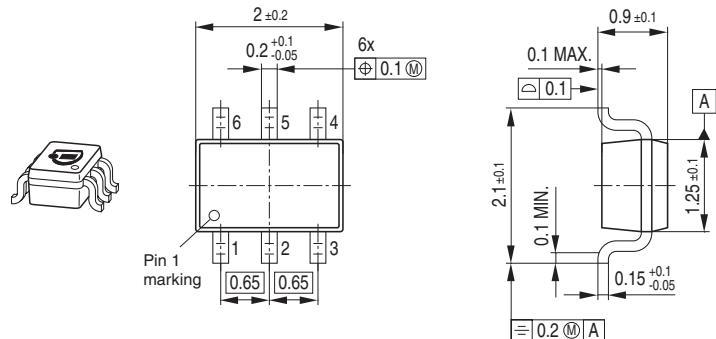


**Permissible Pulse Load**

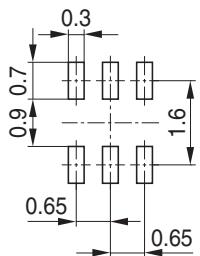
$P_{\text{totmax}} / P_{\text{totDC}} = f(t_p)$



### Package Outline

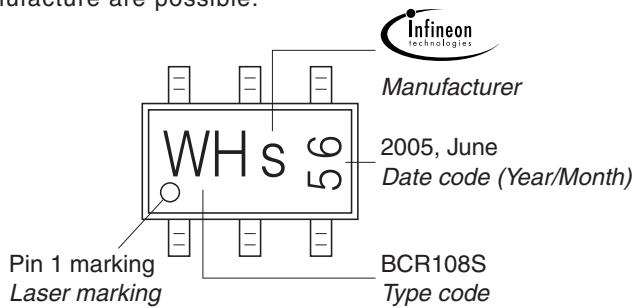


### Foot Print



### Marking Layout (Example)

Small variations in positioning of Date code, Type code and Manufacture are possible.

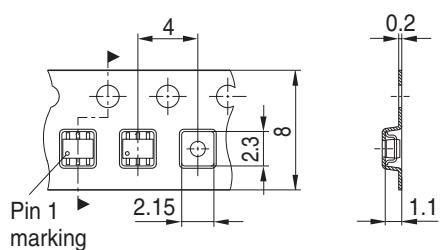


### Standard Packing

Reel ø180 mm = 3.000 Pieces/Reel

Reel ø330 mm = 10.000 Pieces/Reel

For symmetric types no defined Pin 1 orientation in reel.



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